

ZXMN10A07Z

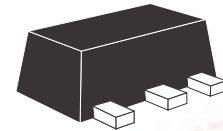
100V N-CHANNEL ENHANCEMENT MODE MOSFET

SUMMARY

$V_{(BR)DSS} = 100V$; $R_{DS(ON)} = 1\Omega$ $I_D = 1.15A$

DESCRIPTION

This new generation of TRENCH MOSFETs from Zetex utilizes a unique structure that combines the benefits of low on-resistance with fast switching speed. This makes them ideal for high efficiency, low voltage, power management applications.



SOT89

FEATURES

- Low on-resistance
- Fast switching speed
- Low threshold
- Low gate drive
- SOT89 package

APPLICATIONS

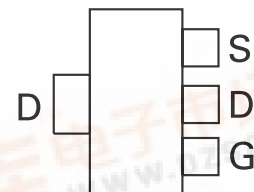
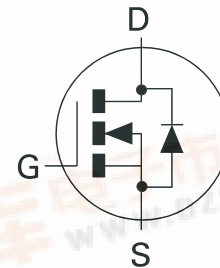
- DC - DC Converters
- Power Management Functions
- Relay and solenoid driving
- Motor control

ORDERING INFORMATION

DEVICE	REEL SIZE	TAPE WIDTH	QUANTITY PER REEL
ZXMN10A07ZTA	7"	12mm	1000 units

DEVICE MARKING

- 7N10



Top View

ZXMN10A07Z

ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	LIMIT	UNIT
Drain-Source Voltage	V_{DSS}	100	V
Gate Source Voltage	V_{GS}	± 20	V
Continuous Drain Current $V_{GS}=10V$; $T_A=25^\circ C$ (b) $V_{GS}=10V$; $T_A=70^\circ C$ (b) $V_{GS}=10V$; $T_A=25^\circ C$ (a)	I_D	1.15 0.92 0.87	A
Pulsed Drain Current (c)	I_{DM}	3.9	A
Continuous Source Current (Body Diode) (b)	I_S	2.1	A
Pulsed Source Current (Body Diode) (c)	I_{SM}	3.9	A
Power Dissipation at $T_A=25^\circ C$ (a) Linear Derating Factor	P_D	1.5 12	W mW/ $^\circ C$
Power Dissipation at $T_A=25^\circ C$ (b) Linear Derating Factor	P_D	2.6 21	W mW/ $^\circ C$
Operating and Storage Temperature Range	$T_j:T_{stg}$	-55 to +150	$^\circ C$

THERMAL RESISTANCE

PARAMETER	SYMBOL	VALUE	UNIT
Junction to Ambient (a)	$R_{\theta JA}$	83.3	$^\circ C/W$
Junction to Ambient (b)	$R_{\theta JA}$	47.4	$^\circ C/W$

NOTES

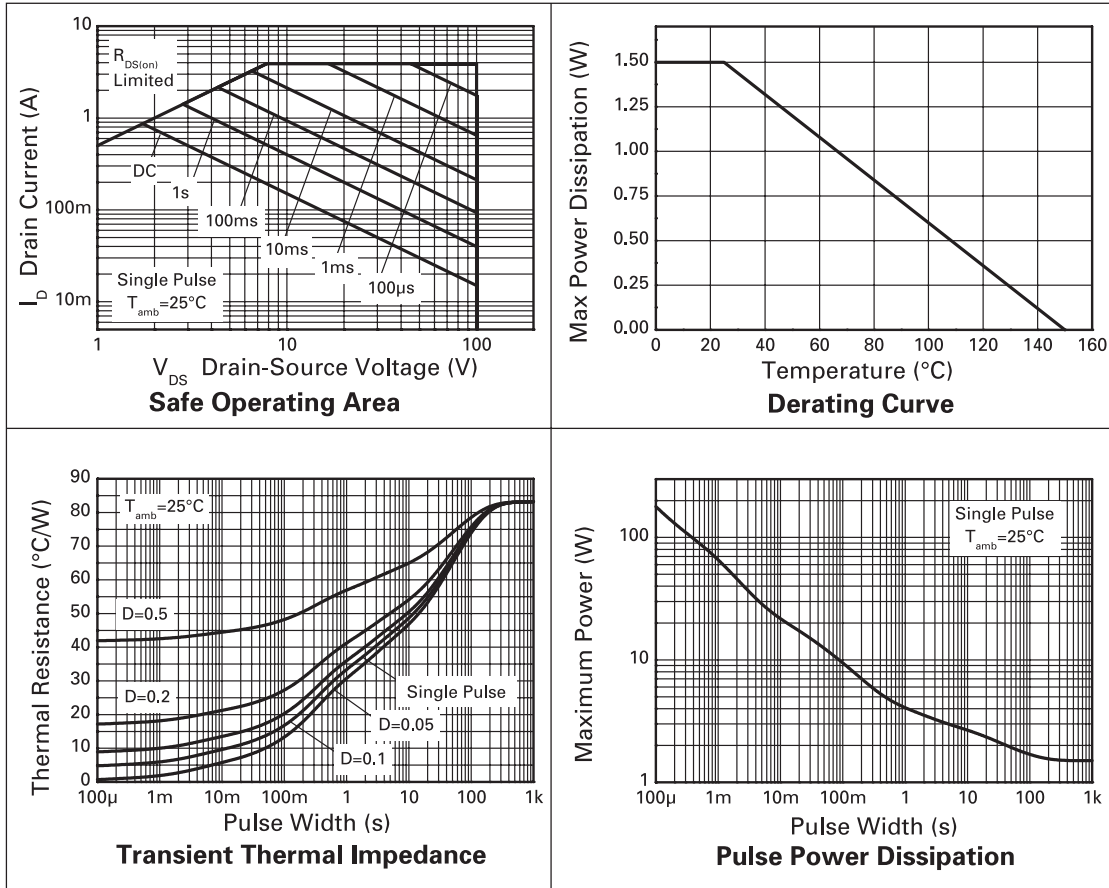
(a) For a device surface mounted on 25mm x 25mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions

(b) For a device surface mounted on FR4 PCB measured at $t \leq 10$ secs.

(c) Repetitive rating 25mm x 25mm FR4 PCB, $D = 0.05$, pulse width $10 \mu s$ - pulse width limited by maximum junction temperature. Refer to transient Thermal Impedance graph

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CHARACTERISTICS



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ELECTRICAL CHARACTERISTICS (at $T_A = 25^\circ\text{C}$ unless otherwise stated).

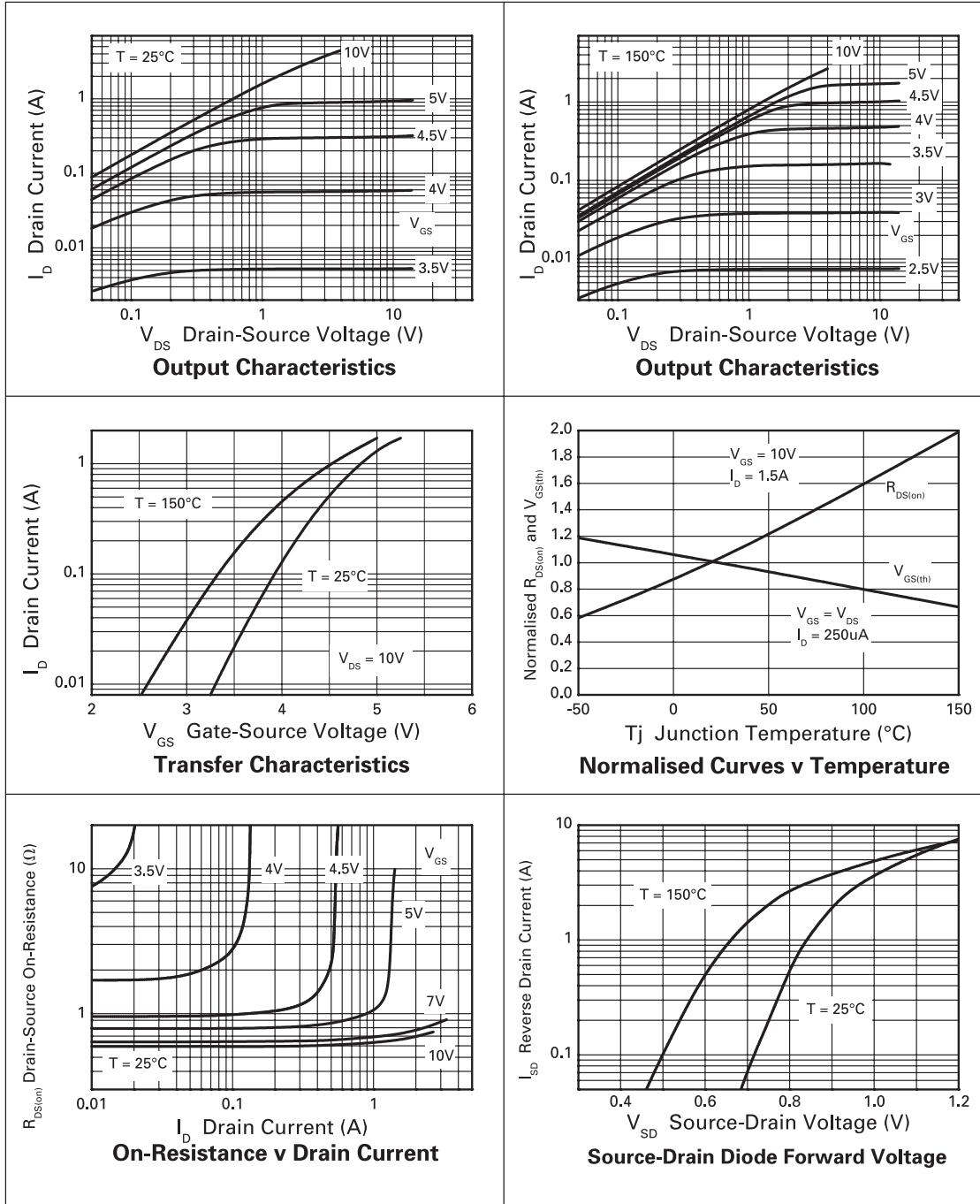
PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
STATIC						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	100			V	$I_D=250\mu\text{A}, V_{GS}=0\text{V}$
Zero Gate Voltage Drain Current	I_{DSS}			1.0	μA	$V_{DS}=100\text{V}, V_{GS}=0\text{V}$
Gate-Body Leakage	I_{GSS}			100	nA	$V_{GS}=\pm 20\text{V}, V_{DS}=0\text{V}$
Gate-Source Threshold Voltage	$V_{GS(th)}$	2.0			V	$I_D=250\mu\text{A}, V_{DS}=V_{GS}$
Static Drain-Source On-State Resistance (1)	$R_{DS(on)}$			1.0 1.1	Ω Ω	$V_{GS}=10\text{V}, I_D=1.5\text{A}$ $V_{GS}=6\text{V}, I_D=1\text{A}$
Forward Transconductance (1)(3)	g_{fs}		1.6		S	$V_{DS}=15\text{V}, I_D=1\text{A}$
DYNAMIC (3)						
Input Capacitance	C_{iss}		138		pF	$V_{DS}=50\text{V}, V_{GS}=0\text{V},$ $f=1\text{MHz}$
Output Capacitance	C_{oss}		12		pF	
Reverse Transfer Capacitance	C_{rss}		6		pF	
SWITCHING(2) (3)						
Turn-On Delay Time	$t_{d(on)}$		1.8		ns	$V_{DD}=50\text{V}, I_D=1.0\text{A}$ $R_G=6.0\Omega, V_{GS}=10\text{V}$
Rise Time	t_r		1.5		ns	
Turn-Off Delay Time	$t_{d(off)}$		4.1		ns	
Fall Time	t_f		2.1		ns	
Total Gate Charge	Q_g		2.9		nC	$V_{DS}=50\text{V}, V_{GS}=10\text{V},$ $I_D=1.0\text{A}$
Gate-Source Charge	Q_{gs}		0.7		nC	
Gate-Drain Charge	Q_{gd}		1.0		nC	
SOURCE-DRAIN DIODE						
Diode Forward Voltage (1)	V_{SD}		0.84	0.95	V	$T_J=25^\circ\text{C}, I_S=1.5\text{A},$ $V_{GS}=0\text{V}$
Reverse Recovery Time (3)	t_{rr}		27		ns	$T_J=25^\circ\text{C}, I_F=1.0\text{A},$ $di/dt=100\text{A}/\mu\text{s}$
Reverse Recovery Charge (3)	Q_{rr}		12		nC	

NOTES

- (1) Measured under pulsed conditions. Width=300 μs . Duty cycle $\leq 2\%$.
- (2) Switching characteristics are independent of operating junction temperature.
- (3) For design aid only, not subject to production testing.

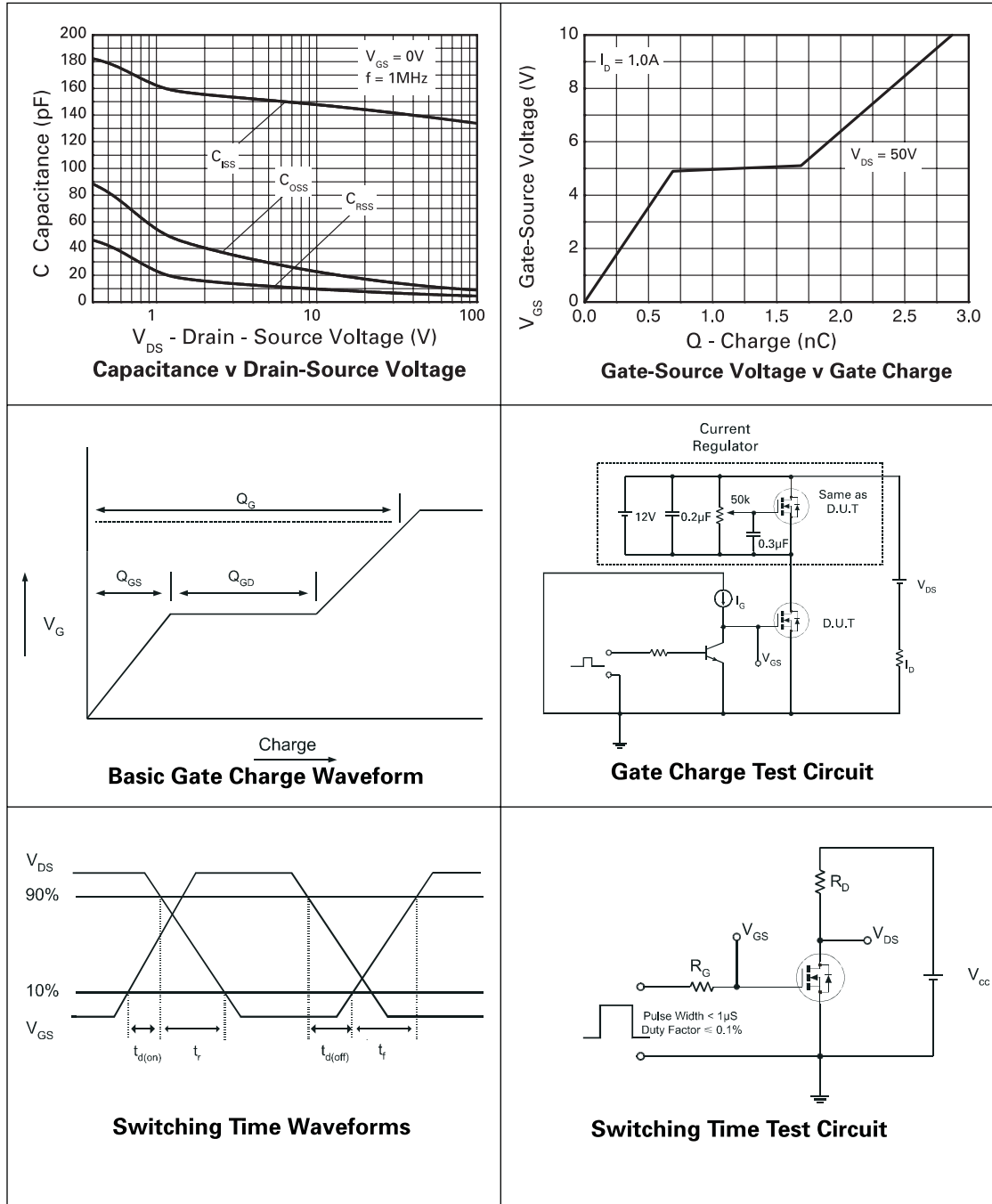
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TYPICAL CHARACTERISTICS



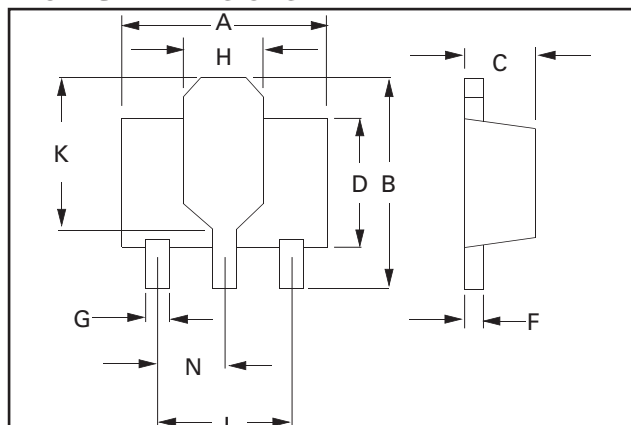
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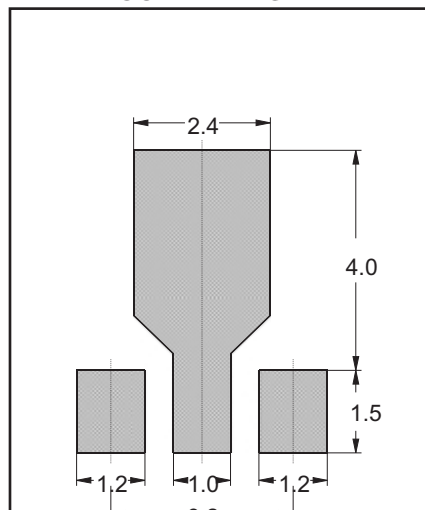


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PACKAGE DIMENSIONS



PAD LAYOUT DETAILS



DIM	Millimetres		Inches	
	Min	Max	Min	Max
A	2.67	3.05	0.105	0.120
B	1.20	1.40	0.047	0.055
C	-	1.10	-	0.043
D	0.37	0.53	0.0145	0.021
F	0.085	0.15	0.0033	0.0059
G	NOM 1.9		NOM 0.075	
K	0.01	0.10	0.0004	0.004
L	2.10	2.50	0.0825	0.0985
N	NOM 0.95		NOM 0.037	

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ISSUE 1 - MARCH 2002

 ZETEX